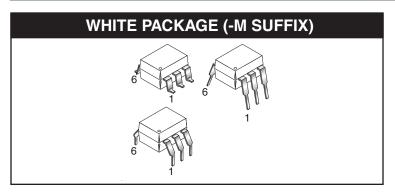
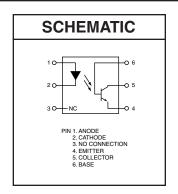
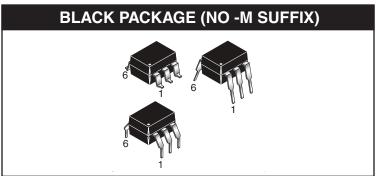


4N25	4N26	4N27	4N28	4N35	4N36
4N37	H11A1	H11A2	H11A3	H11A4	H11A5







DESCRIPTION

The general purpose optocouplers consist of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 6-pin dual in-line package.

FEATURES

- Also available in white package by specifying -M suffix, eg. 4N25-M
- UL recognized (File # E90700)
- VDE recognized (File # 94766)
 - Add option V for white package (e.g., 4N25V-M)
 - Add option 300 for black package (e.g., 4N25.300)

APPLICATIONS

- Power supply regulators
- · Digital logic inputs
- Microprocessor inputs



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise specified)						
Parameter	Symbol	Value	Units			
TOTAL DEVICE						
Storage Temperature	T _{STG}	-55 to +150	°C			
Operating Temperature	T _{OPR}	-55 to +100	°C			
Wave solder temperature (see page 14 for reflow solder profiles)	T _{SOL}	260 for 10 sec	°C			
Total Device Power Dissipation @ T _A = 25°C	P _D	250	mW			
Derate above 25°C	ם י	3.3 (non-M), 2.94 (-M)	IIIVV			
EMITTER						
DC/Average Forward Input Current	I _F	100 (non-M), 60 (-M)	mA			
Reverse Input Voltage	V _R	6	V			
Forward Current - Peak (300µs, 2% Duty Cycle)	I _F (pk)	3	А			
LED Power Dissipation @ T _A = 25°C	P _D	150 (non-M), 120 (-M)	mW			
Derate above 25°C	ט' ט	2.0 (non-M), 1.41 (-M)	mW/°C			
DETECTOR						
Collector-Emitter Voltage	V _{CEO}	30	V			
Collector-Base Voltage	V _{CBO}	70	V			
Emitter-Collector Voltage	V _{ECO}	7	V			
Detector Power Dissipation @ T _A = 25°C	P-	150	mW			
Derate above 25°C	P _D	2.0 (non-M), 1.76 (-M)	mW/°C			



4N25	4N26	4N27	4N28	4N35	4N36
4N37	H11A1	H11A2	H11A3	H11A4	H11A5

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

INDIVIDUAL COMPONENT CHARACTERISTICS							
Parameter	Test Conditions	Symbol	Min	Тур*	Max	Unit	
EMITTER							
Input Forward Voltage	(I _F = 10 mA)	V_{F}		1.18	1.50	V	
Reverse Leakage Current	$(V_{R} = 6.0 \text{ V})$	I _R		0.001	10	μΑ	
DETECTOR							
Collector-Emitter Breakdown Voltage	$(I_C = 1.0 \text{ mA}, I_F = 0)$	BV_CEO	30	100		V	
Collector-Base Breakdown Voltage	$(I_C = 100 \mu A, I_F = 0)$	BV _{CBO}	70	120		V	
Emitter-Collector Breakdown Voltage	$(I_E = 100 \mu A, I_F = 0)$	BV _{ECO}	7	10		V	
Collector-Emitter Dark Current	$(V_{CE} = 10 \text{ V}, I_F = 0)$	I _{CEO}		1	50	nA	
Collector-Base Dark Current	(V _{CB} = 10 V)	I _{CBO}			20	nA	
Capacitance	(V _{CE} = 0 V, f = 1 MHz)	C _{CE}		8		pF	

ISOLATION CHARACTERISTICS								
Characteristic	Test Conditions	Symbol	Min	Тур*	Max	Units		
logue Outrout logistics Valtage	(Non '-M', Black Package) (f = 60 Hz, t = 1 min)	V	5300			Vac(rms)		
Input-Output Isolation Voltage	('-M', White Package) (f = 60 Hz, t = 1 sec)	V _{ISO}	7500			Vac(pk)		
Isolation Resistance	$(V_{I-O} = 500 \text{ VDC})$	R _{ISO}	10 ¹¹			Ω		
Isolation Capacitance	$(V_{I-O} = \&, f = 1 MHz)$			0.5		pF		
Isolation Capacitance	('-M' White Package)	C _{ISO}	·	0.2	2	pF		

Note

^{*} Typical values at $T_A = 25$ °C



TRANSFER CHARACTERISTICS (T _A = 25°C Unless otherwise specified.)							
DC Characteristic	Test Conditions	Symbol	Device	Min	Тур*	Max	Unit
			4N35 4N36 4N37	100			
			H11A1	50			
			H11A5	30			
	$(I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V})$	CTR	4N25 4N26 H11A2 H11A3	20			%
Current Transfer Ratio, Collector to Emitter			4N27 4N28 H11A4	10			70
	$(I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V}, T_A = -55^{\circ}\text{C})$		4N35 4N36 4N37	40			
	$(I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V}, T_A = +100^{\circ}\text{C})$		4N35 4N36 4N37	40			
	$(I_C = 2 \text{ mA}, I_F = 50 \text{ mA})$		4N25 4N26 4N27 4N28			0.5	
Collector-Emitter Saturation Voltage		V _{CE (SAT)}	4N35 4N36 4N37			0.3	V
	$(I_C = 0.5 \text{ mA}, I_F = 10 \text{ mA})$		H11A1 H11A2 H11A3 H11A4 H11A5			0.4	
AC Characteristic Non-Saturated Turn-on Time	$(I_F = 10 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100\Omega)$ (Fig.20)	T _{ON}	4N25 4N26 4N27 4N28 H11A1 H11A2 H11A3 H11A4 H11A5		2		μѕ
Non Saturated Turn-on Time	$(I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100\Omega)$ (Fig.20)	T _{ON}	4N35 4N36 4N37		2	10	μs



AC Characteristic	Test Conditions	Symbol	Device	Min	Тур*	Max	Unit
Turn-off Time	$(I_F = 10 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100\Omega)$ (Fig.20)	T _{OFF}	4N25 4N26 4N27 4N28 H11A1 H11A2 H11A3 H11A4 H11A5		2		μs
	$(I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100\Omega)$ (Fig.20)		4N35 4N36		2	10	

^{*} Typical values at $T_A = 25$ °C



4N25 4N26 4N37 H11A1

4N27 H11A2 4N28 H11A3 4N35 H11A4 4N36 H11A5

TYPICAL PERFORMANCE CURVES

Fig. 1 LED Forward Voltage vs. Forward Current (Black Package)

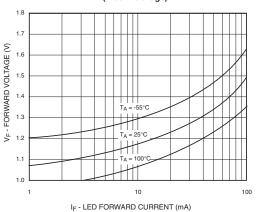


Fig. 2 LED Forward Voltage vs. Forward Current (White Package)

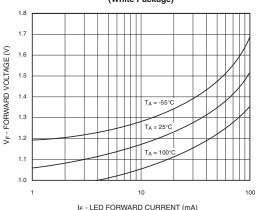


Fig.3 Normalized CTR vs. Forward Current (Black Package)

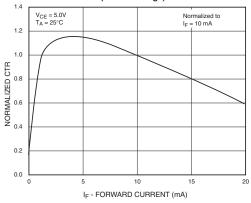


Fig.4 Normalized CTR vs. Forward Current (White Package)

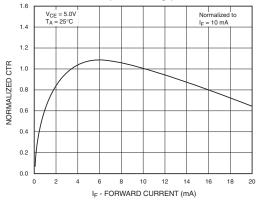


Fig. 5 Normalized CTR vs. Ambient Temperature

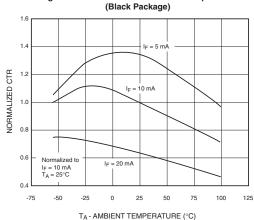
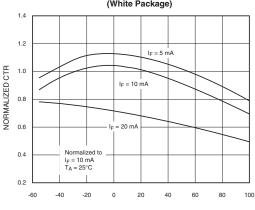
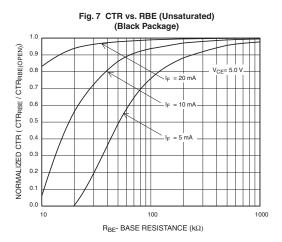


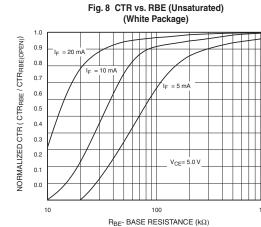
Fig. 6 Normalized CTR vs. Ambient Temperature (White Package)

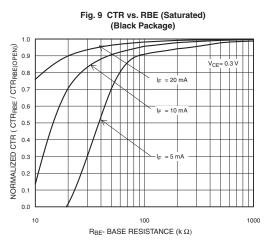


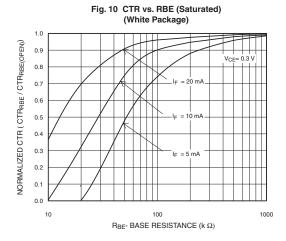


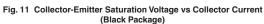
4N25 4N37 4N26 H11A1 4N27 H11A2 4N28 H11A3 4N35 H11A4 4N36 H11A5











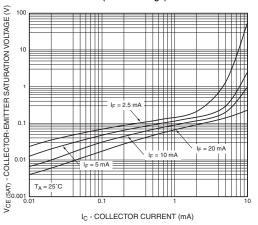
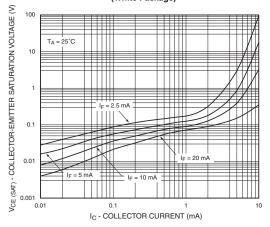


Fig. 12 Collector-Emitter Saturation Voltage vs Collector Current (White Package)





4N25 4N37 4N26 H11A1 4N27 H11A2 4N28 H11A3 4N35 H11A4 4N36 H11A5

Fig. 13 Switching Speed vs. Load Resistor (Black Package)

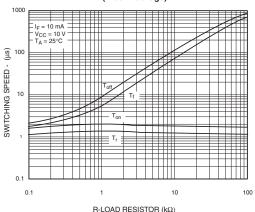


Fig. 14 Switching Speed vs. Load Resistor (White Package)

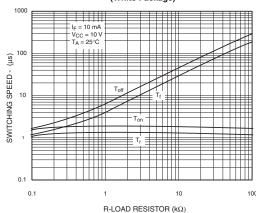


Fig. 15 Normalized t_{on} vs. R_{BE} (Black Package)

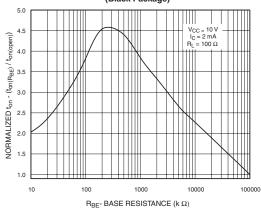


Fig. 16 Normalized t_{on} vs. R_{BE} (White Package)

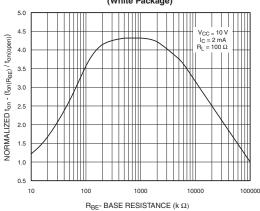


Fig. 17 Normalized toff vs. R_{BE}

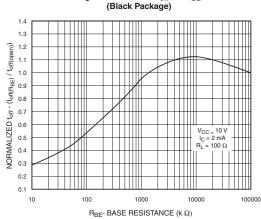
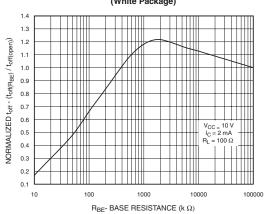


Fig. 18 Normalized t_{off} vs. R_{BE} (White Package)





4N25	4N26	4N27	4N28	4N35	4N36
4N37	H11A1	H11A2	H11A3	H11A4	H11A5

Fig. 19 Dark Current vs. Ambient Temperature

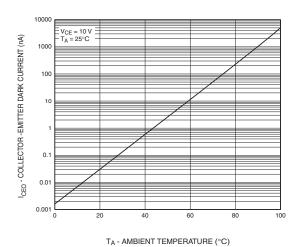


Figure 20. Switching Time Test Circuit and Waveforms

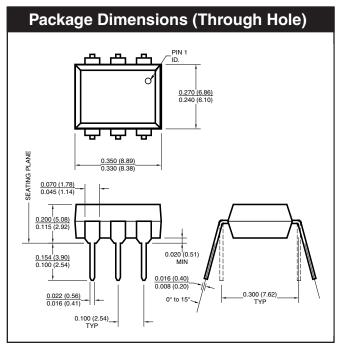
Adjust I_F to produce $I_C = 2 \text{ mA}$

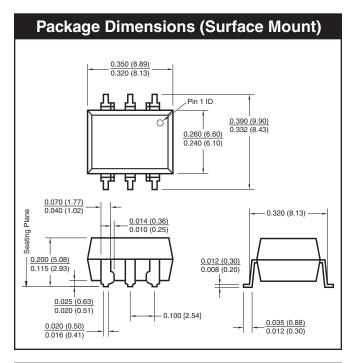


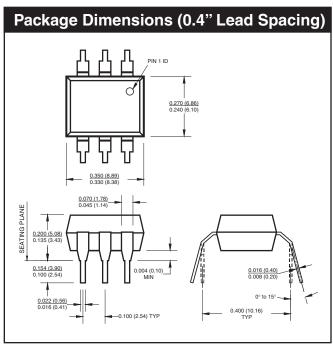
 4N25
 4N26
 4N27
 4N28
 4N35
 4N36

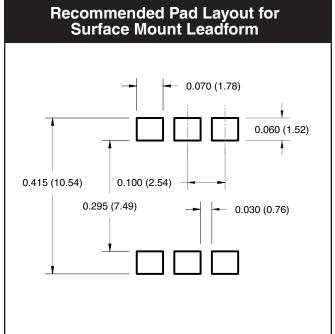
 4N37
 H11A1
 H11A2
 H11A3
 H11A4
 H11A5

Black Package (No -M Suffix)









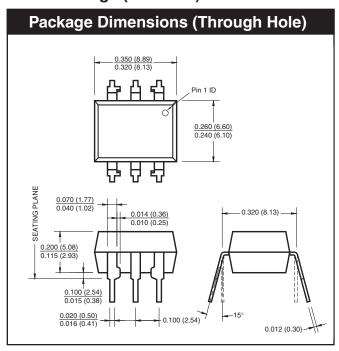
NOTE All dimensions are in inches (millimeters)

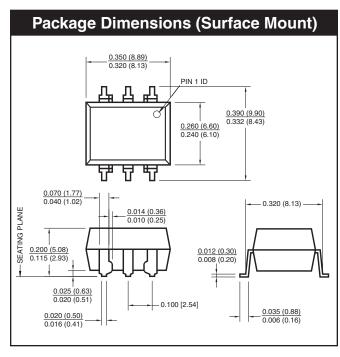


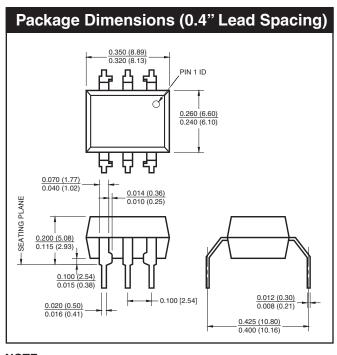
 4N25
 4N26
 4N27
 4N28
 4N35
 4N36

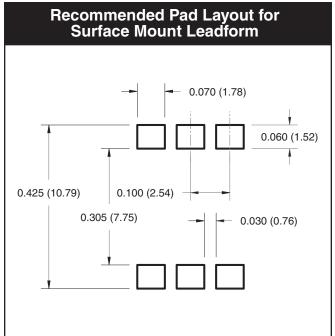
 4N37
 H11A1
 H11A2
 H11A3
 H11A4
 H11A5

White Package (-M Suffix)









NOTEAll dimensions are in inches (millimeters)

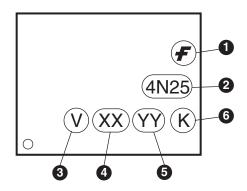


4N25	4N26	4N27	4N28	4N35	4N36
4N37	H11A1	H11A2	H11A3	H11A4	H11A5

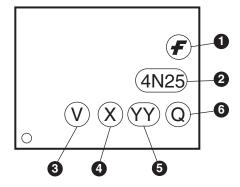
ORDERING INFORMATION

Order Entry Identifier						
Black Package (No Suffix)	White Package (-M Suffix)	Option				
.S	S	Surface Mount Lead Bend				
.SD	SR2	Surface Mount; Tape and reel				
.W	Т	0.4" Lead Spacing				
.300	V	VDE 0884				
.300W	TV	VDE 0884, 0.4" Lead Spacing				
.3\$	SV	VDE 0884, Surface Mount				
.3SD	SR2V	VDE 0884, Surface Mount, Tape & Reel				

MARKING INFORMATION



Black Package, No Suffix

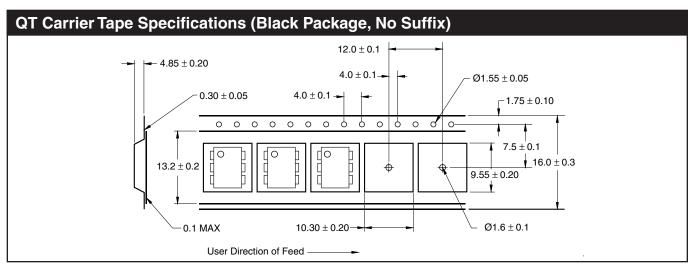


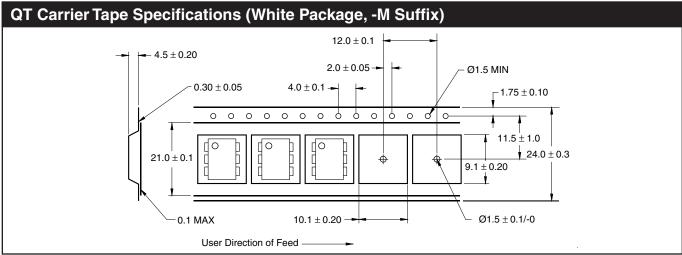
White Package, -M Suffix

Definitions						
1	Fairchild logo					
2	Device number					
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)					
4	One or two digit year code Two digits for black package parts, e.g., '03' One digit for white package parts, e.g., '3'					
5	Two digit work week ranging from '01' to '53'					
6	Assembly package code					

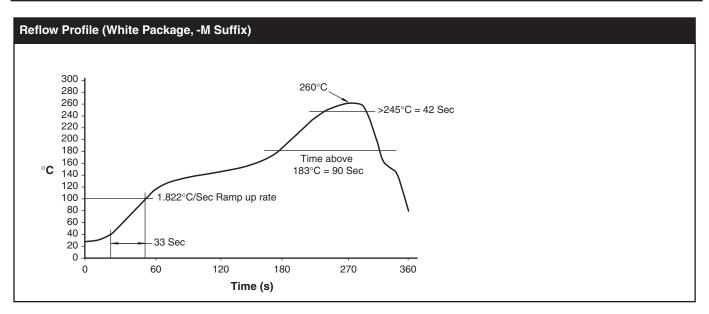
^{*}Note – Parts built in the white package (M suffix) that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in the portrait format.

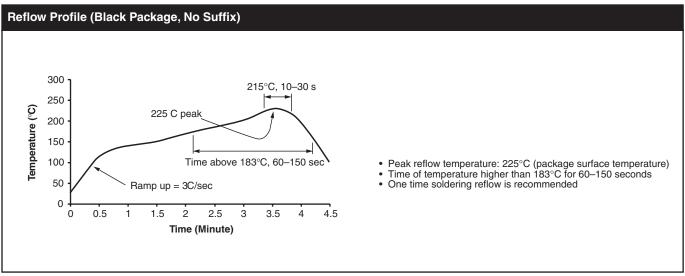














4N25	4N26	4N27	4N28	4N35	4N36
4N37	H11A1	H11A2	H11A3	H11A4	H11A5

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor:

H11A2SVM H11A5TVM H11A2SM H11A4VM H11A4TM H11A5SM H11A5TM H11A5TVM H11A5SVM H11A2SR2VM H11A4M H11A2SR2M H11A3SM H11A3VM H11A3TM H11A4SR2VM H11A5SR2VM H11A5SR2VM H11A5SR2VM H11A5SR2VM H11A5SR2VM H11A3SVM H11A4TVM H11A2TVM H11A3SR2VM H11A2TVM H11A4SR2M H11A3SR2VM H11A2TVM H11A4SR2M H11A3SR2VM H11A3TVM 4N35300W 4N27 H11A5W 4N36300 4N37300W 4N263SD 4N28S H11A5 4N27TM H11A4 4N253S 4N27S H11A5_Q H11A4SVM 4N28TM 4N26300W 4N25TM H11A23SD 4N25FVM H11A4_Q H11A3_Q H11A23S 4N273S 4N35SW 4N37300 4N25W 4N363SD H11A1FM H11A5SD H11A5S H11A53SD H11A1300W 4N353S 4N353SD 4N35TM 4N37FR2VM 4N253SD 4N26300 4N27FR2M 4N26FM 4N37S_Q 4N36S H11A1300_Q 4N26S H11A1W 4N26 4N36FVM 4N28300W 4N36SD 4N36FR2VM 4N25FR2M H11A3SD H11A5SS H11A33SD 4N25S_Q 4N27FM 4N28FR2VM H11A4SD 4N36S_Q 4N26FVM 4N35S H11A4SM 4N26FR2M 4N28300 H11A3300W 4N37W H11A1FR2M H11A2FR2M 4N26S 4N36FR2M H11A43SD 4N26W H11A2300